



#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	5.5mΩ @ V <sub>GS</sub> = 10V	15A
30V	7.5mΩ @ V <sub>GS</sub> = 4.5V	12A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **30V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Features and Benefits**

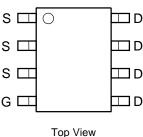
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

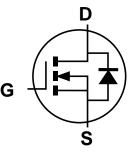
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)



Top View



I op View Internal Schematic



Equivalent Circuit

## Ordering Information (Note 4)

-		
Part Number	Case	Packaging
DMN3009SSS-13	SO-8	2500/Tape & Reel

Notes:

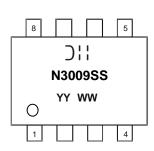
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



)|| = Manufacturer's Marking N3009SS = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 19 = 2019) WW = Week (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) $V_{GS}$ = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	15 12	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	80	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	2.7	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	33	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	55	mJ

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	Steady State	T <sub>A</sub> = +25°C	PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	R <sub>ÐJA</sub>	101	°C/W
Total Power Dissipation (Note 6)	Steady State	T <sub>A</sub> = +25°C	PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	R <sub>ÐJA</sub>	73	°C/W
Thermal Resistance, Junction to Case (Note 6)			Rejc	7.6	0/00
Operating and Storage Temperature Range			T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	_	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.5	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	4.5	5.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	5.5	7.5	11122	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.75	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)	·					*	
Input Capacitance	Ciss		2,000	—	рF		
Output Capacitance	Coss	_	315	_	pF	<sup>−</sup> V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, − f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	247	—	pF	1 = 1.00012	
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	20	—	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	42	_	nC		
Gate-Source Charge	Q <sub>gs</sub>	_	4.7	—	nC	$V_{DS} = 15V, I_D = 15A$	
Gate-Drain Charge	Q <sub>qd</sub>	_	7.4	_	nC	7	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.9	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	4.1	_	ns	$V_{DD} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		31	—	ns	$R_{G} = 3.3\Omega, I_{D} = 15A$	
Turn-Off Fall Time	t <sub>F</sub>		15	_	ns	7	
Reverse Recovery Time	t <sub>RR</sub>	_	15	—	ns		
Reverse Recovery Charge	Q <sub>RR</sub>		6.0	—	nC	$I_F = 15A$ , di/dt = 100A/µs	

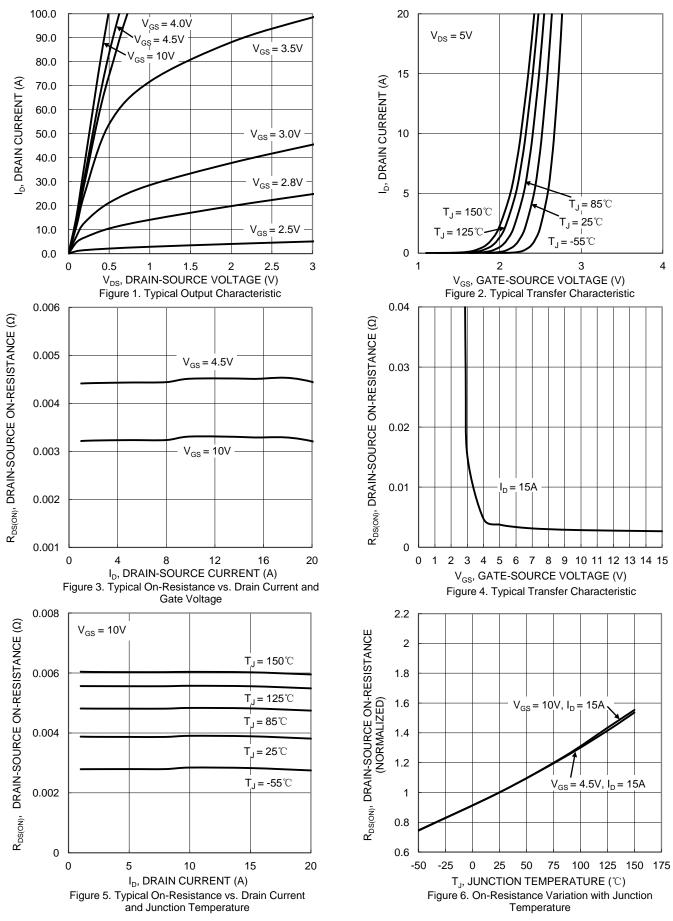
5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout. Notes:

6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.

5. Device information of the state of the s



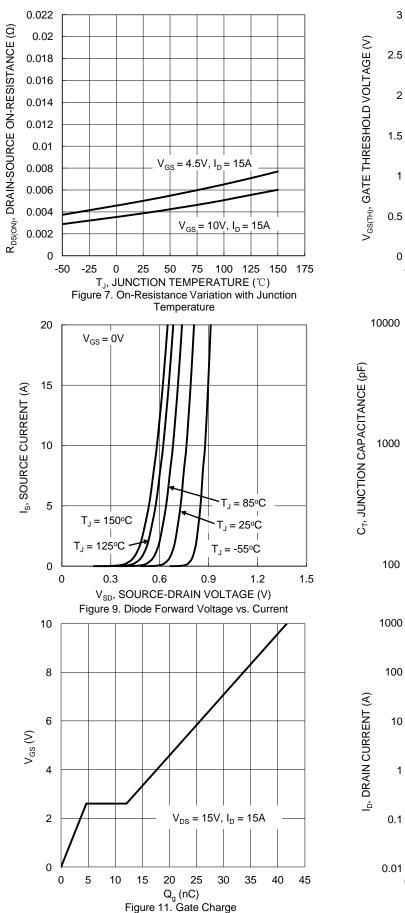
### **DMN3009SSS**

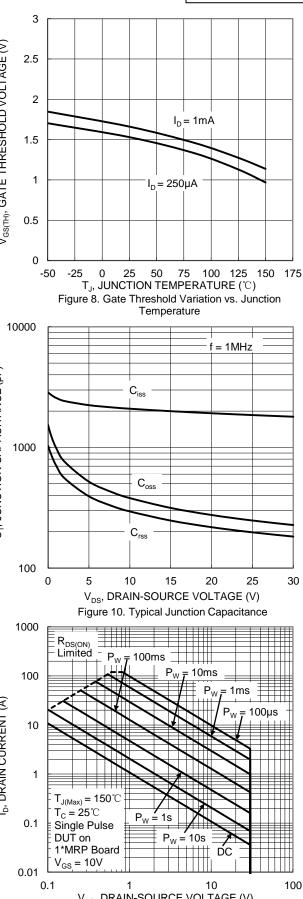


DMN3009SSS Document number: DS40792 Rev. 4 - 2



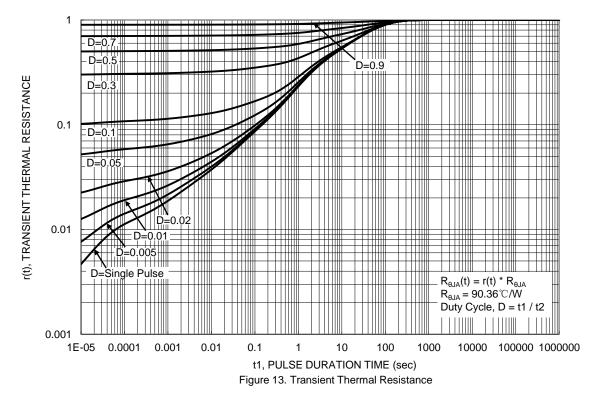
### **DMN3009SSS**





V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

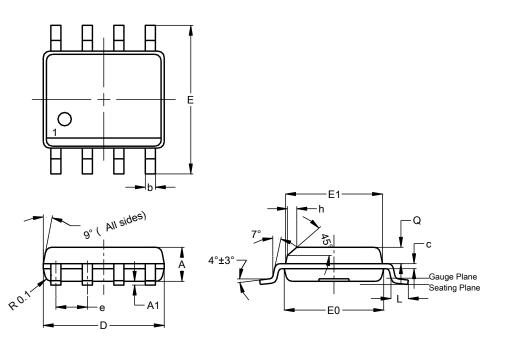






# **Package Outline Dimensions**

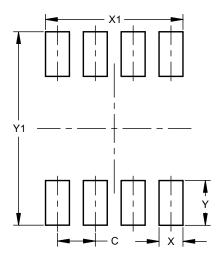
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8					
Dim	Min Max Ty		Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
E	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h			0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8

SO-8

Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Y	1.505
Y1	6.50



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